

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|---|--------------------------------|------------------|---------|------------------|
| L1 | 6 | FinFET near10 (source near5 drain near5 channel) | USPAT; EPO; JPO; DERWENT | OR | OFF | 2004/12/03 18:46 |

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|--------|--|--------------------------|------------------|---------|------------------|
| L1 | 109099 | SOI and substrate near5 silicon adj carbide and dielectric layer and gate and insulat\$3 | USPAT; EPO; JPO; DERWENT | OR | OFF | 2004/12/03 17:54 |
| L2 | 109112 | SOI and substrate near5 silicon adj carbide and dielectric layer and gate and insulat\$3 | USPAT; EPO; JPO; DERWENT | OR | OFF | 2004/12/03 17:54 |
| L3 | 109119 | SOI and substrate near5 (silicon adj carbide) and dielectric layer and gate and insulat\$3 | USPAT; EPO; JPO; DERWENT | OR | OFF | 2004/12/03 17:55 |
| L4 | 12 | SOI and substrate near5 (silicon adj carbide) and dielectric adj layer and gate and insulat\$3 | USPAT; EPO; JPO; DERWENT | OR | OFF | 2004/12/03 17:55 |